SRM2B256SLMX55/70/10

256K-BIT STATIC RAM

- **Wide Temperature Range**
- **Extremely Low Standby Current**
- **Access Time 100ns (2.7V) 55ns (4.5V)**
- **32,768 Words × 8-Bit Asynchronous**

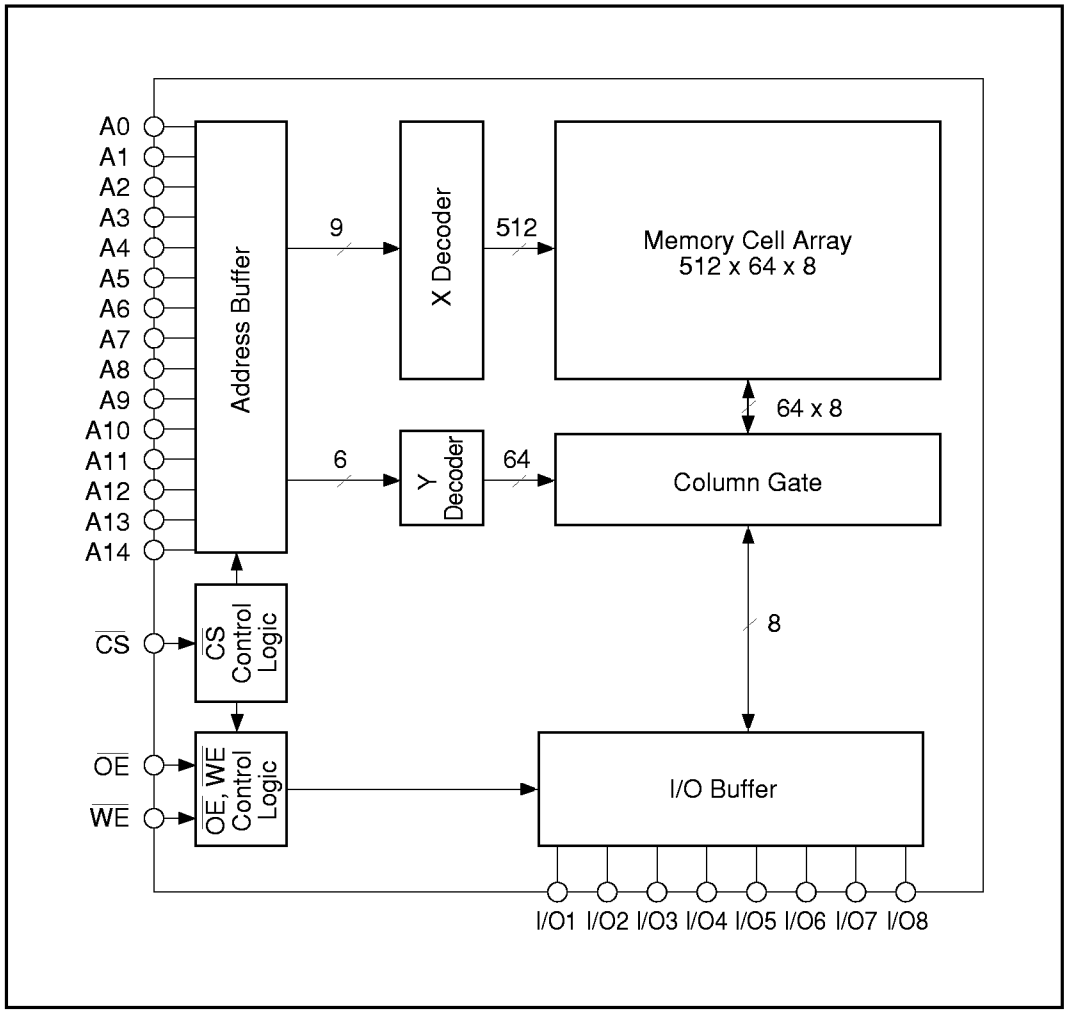
■ DESCRIPTION

The SRM2B256SLMX is a low voltage operating 32,768 words × 8-bit asynchronous, static, random access memory fabricated using an advanced CMOS technology. Its very low standby power consumption makes it ideal for applications requiring non-volatile storage with back-up batteries, and –25 to 85°C operating temperature range makes it ideal for industrial use. The asynchronous and static nature of the memory requires no external clock or refresh circuit. 3-state output ports allow easy expansion of memory capacity. These features make the SRM2B256SLMX usable for a wide range of applications, from microprocessor systems to terminal devices.

■ FEATURES

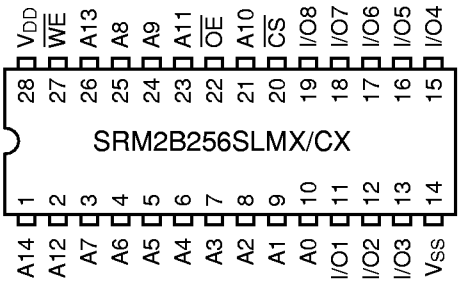
- Wide temperature range . . . . . –25 to 85°C
- Extended supply voltage range. . . . . 2.7 to 5.5V
- Fast access time . . . . . 100ns (3V ± 10%)
  55ns (5V ± 10%)
- Extremely low standby current . . . . . SL Version
- Completely static. . . . . No clock required
- 3-state output
- Battery back-up operation
- Package . . . . . SRM2B256SLCX . . . . . DIP2-28pin (plastic)
  SRM2B256SLMX . . . . . SOP2-28pin (plastic)
  SRM2B256SLTMX . . . . . TSOP (I)-28pin (plastic)
  SRM2B256SLRMX. . . . . TSOP (I)-28pin-R1 (plastic)

■ BLOCK DIAGRAM

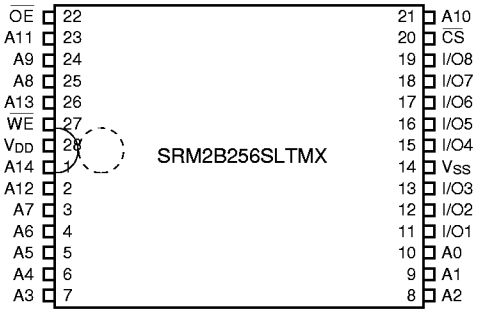


■ PIN CONFIGURATION

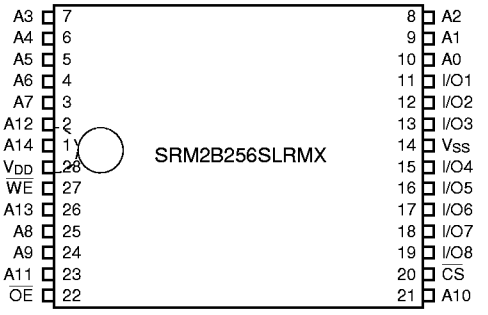
(DIP/SOP2)



(TSOP)



(TSOP-R1)(Reverse bending)



■ PIN DESCRIPTION

A0 to A14	Address input
$\overline{WE}$	Write Enable
$\overline{OE}$	Output Enable
$\overline{CS}$	Chip Select
I/O1 to I/O8	Data I/O
V_{DD}	Power Supply (2.7V to 5.5V)
V_{SS}	Power Supply (0V)

■ ABSOLUTE MAXIMUM RATINGS

V_{SS} = 0V

Parameter	Symbol	Rating	Unit
Supply voltage	V_{DD}	–0.5 to 7.0	V
Input voltage	V_I	–0.5* to 7.0	V
Input/output voltage	$V_{I/O}$	–0.5* to V_{DD} + 0.3	V
Power dissipation	P_D	1.0	W
Operating temperature	T_{OPR}	–25 to 85	°C
Storage temperature	T_{STG}	–65 to 150	°C
Soldering temperature and time	T_{SOL}	260°C, 10s (Lead only)	—

* V_I, $V_{I/O}$ (Min.) = –3.0V when pulse width is less or equal to 50ns

■ DC RECOMMENDED OPERATING CONDITIONS

V_{SS} = 0V, T_a = –25 to 85°C

Parameter	Symbol	V_{DD} = 3V ± 10%			V_{DD} = 5V ± 10%			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
Supply voltage	V_{DD}	2.7	—	3.3	4.5	—	5.5	V
	V_{SS}	0	—	0	0	—	0	V
Input voltage	V_{IH}	2.2	—	V_{DD} + 0.3	2.2	—	V_{DD} + 0.3	V
	V_{IL}	–0.3*	—	0.4	–0.3*	—	0.8	V

* V_{IL} (Min.) = –3V when pulse width is less or equal to 50ns

■ ELECTRICAL CHARACTERISTICS

● DC Electrical Characteristics

(V_{SS} = 0V, T_a = –25 to 85°C)

Parameter	Symbol	Conditions	V_{DD} = 3V±10%			V_{DD} = 5V±10%			Unit
			Min	Typ*1	Max	Min	Typ*2	Max	
Input leakage	I_{LI}	V_I = 0 to V_{DD}	–1	—	1	–1	—	1	µA
Standby supply current	I_{DDS}	$\overline{CS}$ = V_{IH}	—	—	2	—	—	3.0	mA
	I_{DDS1}	$\overline{CS}$ ≥ V_{DD} – 0.2V	—	0.3	25	—	0.5	50	µA
Average operating current	I_{DDA}	V_I = V_{IL}, V_{IH} $I_{I/O}$ = 0mA, t_{CYC} = Min	—	10	15	—	30	45	mA
	I_{DDA1}	V_I = V_{IL}, V_{IH} $I_{I/O}$ = 0mA, t_{CYC} = 1µs	—	—	5	—	—	10	mA
Operating supply current	I_{DDO}	V_I = V_{IL}, V_{IH} I_{LO} = 0mA	—	—	5	—	—	10	mA
Output leakage	I_{LO}	$\overline{CS}$ = V_{IH} or $\overline{WE}$ = V_{IL} or $\overline{OE}$ = V_{IH}, $V_{I/O}$ = 0 to V_{DD}	–1	—	1	–1	—	1	µA
High level output voltage	V_{OH}	I_{OH} = –1.0mA, –0.5mA*3	2.4	—	—	2.4	—	—	V
Low level output voltage	V_{OL}	I_{OL} = 2.1mA, 1.0mA*3	—	—	0.4	—	—	0.4	V

*1 Typical values are measured at T_a = 25°C and V_{DD} = 3.0V

*2 Typical values are measured at T_a = 25°C and V_{DD} = 5.0V

*3 V_{DD} = 3.0V±10%

● Terminal Capacitance

(f = 1MHz, T_a = 25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Address capacitance	C_{ADD}	V_{ADD} = 0V	—	—	8	pF
Input capacitance	C_I	V_I = 0V	—	—	8	pF
I/O capacitance	$C_{I/O}$	$V_{I/O}$ = 0V	—	—	10	pF

● AC Electrical Characteristics

○ Read Cycle

V_{SS} = 0V, Ta = –25 to 85°C

Parameter	Symbol	Condi-tions	SRM2B256SLMX55				SRM2B256SLMX70				SRM2B256SLMX10				Unit
			V_{DD} = 3V ±10%		V_{DD} = 5V ±10%		V_{DD} = 3V ±10%		V_{DD} = 5V ±10%		V_{DD} = 3V ±10%		V_{DD} = 5V ±10%		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read cycle time	t_{RC}	*1	100	—	55	—	120	—	70	—	180	—	100	—	nS
Address access time	t_{ACC}		—	100	—	55	—	120	—	70	—	180	—	100	nS
$\overline{CS}$ access time	t_{ACS}		—	100	—	55	—	120	—	70	—	180	—	100	nS
$\overline{OE}$ access time	t_{OE}		—	60	—	30	—	70	—	35	—	90	—	45	nS
$\overline{CS}$ output set time	t_{CLZ}	*2	15	—	10	—	15	—	10	—	15	—	10	—	nS
$\overline{CS}$ output floating	t_{CHZ}		—	35	—	20	—	40	—	25	—	50	—	35	nS
$\overline{OE}$ output set time	t_{OLZ}		5	—	0	—	5	—	0	—	5	—	0	—	nS
$\overline{OE}$ output floating	t_{OHZ}		—	35	—	20	—	40	—	25	—	50	—	35	nS
Output hold time	t_{OH}	*1	15	—	10	—	15	—	10	—	15	—	10	—	nS

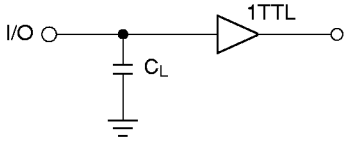
○ Write Cycle

V_{SS} = 0V, Ta = –25 to 85°C

Parameter	Symbol	Condi-tions	SRM2B256SLMX55				SRM2B256SLMX70				SRM2B256SLMX10				Unit
			V_{DD} = 3V ±10%		V_{DD} = 5V ±10%		V_{DD} = 3V ±10%		V_{DD} = 5V ±10%		V_{DD} = 3V ±10%		V_{DD} = 5V ±10%		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Write cycle time	t_{WC}	*1	100	—	55	—	120	—	70	—	180	—	100	—	nS
Chip Select time	t_{CW}		80	—	50	—	90	—	60	—	110	—	80	—	nS
Address valid to end of write	t_{AW}		80	—	50	—	90	—	60	—	110	—	80	—	nS
Address setup time	t_{AS}		0	—	0	—	0	—	0	—	0	—	0	—	nS
Write pulse width	t_{WP}		75	—	40	—	80	—	45	—	100	—	60	—	nS
Address hold time	t_{WR}		0	—	0	—	0	—	0	—	0	—	0	—	nS
Input data set time	t_{DW}		40	—	25	—	45	—	30	—	60	—	40	—	nS
Input data hold time	t_{DH}		0	—	0	—	0	—	0	—	0	—	0	—	nS
Write to output floating	t_{WHZ}	*2	—	35	—	20	—	40	—	25	—	50	—	35	nS
Output active from end to write	t_{OW}		5	—	5	—	5	—	5	—	5	—	5	—	nS

***1. Test Conditions**

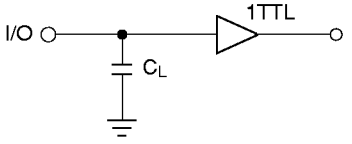
1. Input pulse level: 0.6V to 2.4V (5V) /0.4V to 2.2V (3V)
2. tr = tr = 5ns
3. Input and output timing reference levels : 1.5V
4. Output load C_L = 100pF



C_L = 100pF (Includes Jig Capacitance)

***2. Test Conditions**

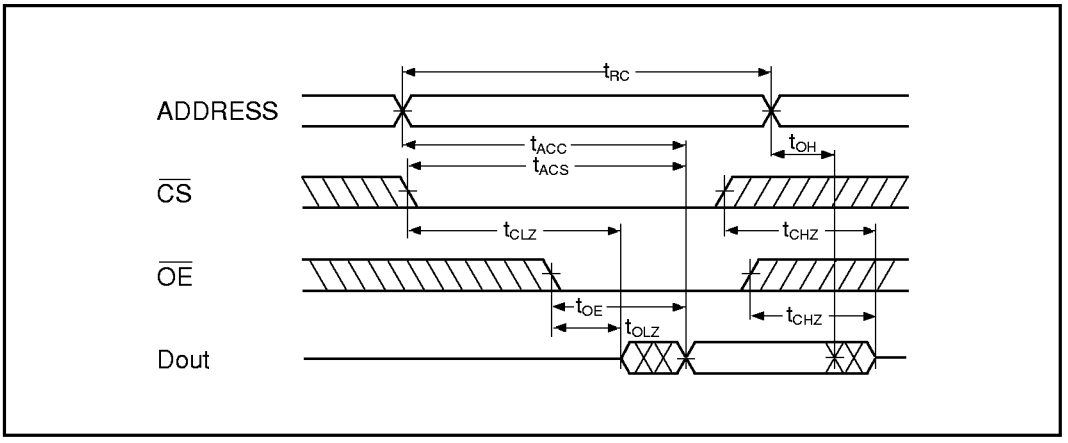
1. Input pulse level: 0.6V to 2.4V (5V) /0.4V to 2.2V (3V)
2. tr = tr = 5ns
3. Input timing reference levels : 1.5V
4. Output timing reference levels: ± 200mV (the level displaced from stable output voltage level)
5. Output load C_L = 5pF



C_L = 5pF (Includes Jig Capacitance)

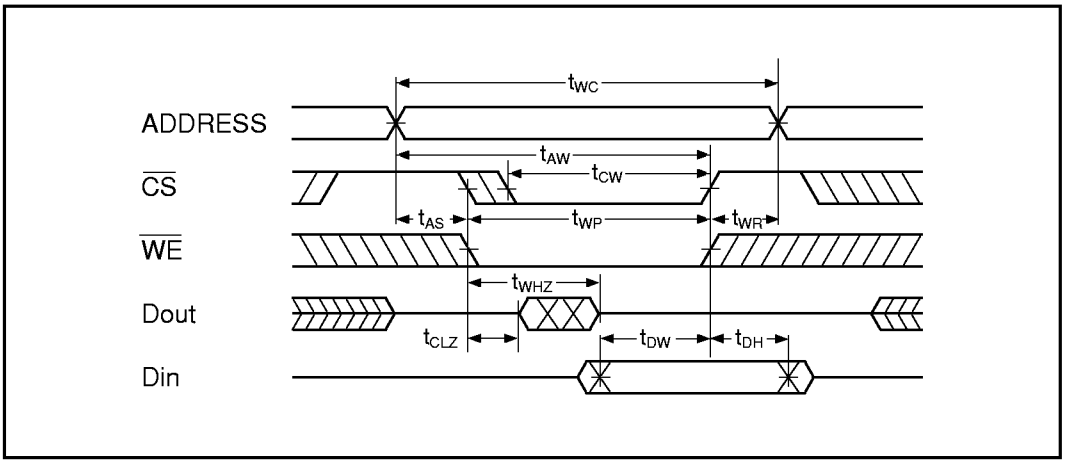
■ Timing Charts

● Read Cycle*1



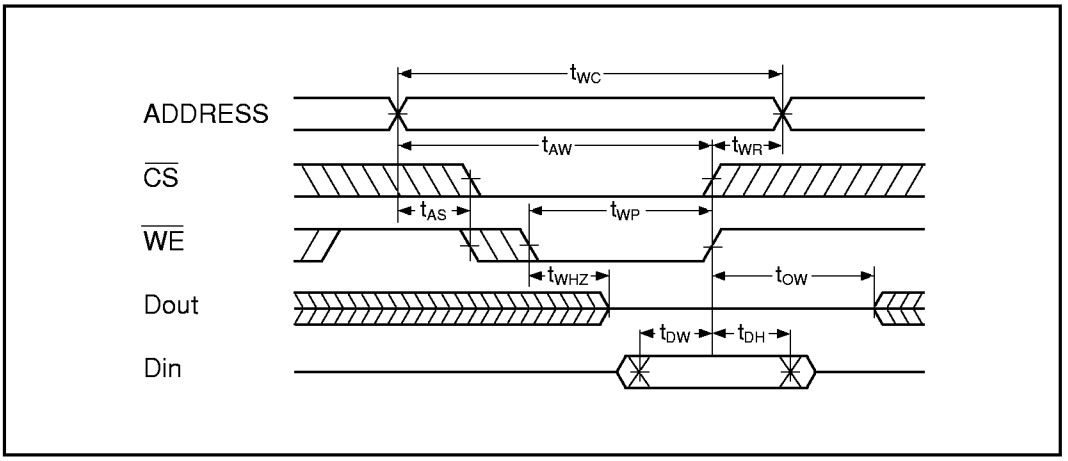
Note: *1. During read cycle time, $\overline{WE}$ must be "H" level.

● Write Cycle (1) ($\overline{CS}$ Control)*2



Note: *2. During write cycle that is controlled by $\overline{CS}$, Output Buffer is in high impedance state, whether $\overline{OE}$ level is "H" or "L".

● **Write Cycle (2) ($\overline{WE}$ Control)*3**



Note: *3. During write cycle that is controlled by $\overline{WE}$, Output Buffer is in high impedance state if $\overline{OE}$ is "H" level.

■ DATA RETENTION CHARACTERISTIC WITH LOW VOLTAGE POWER SUPPLY

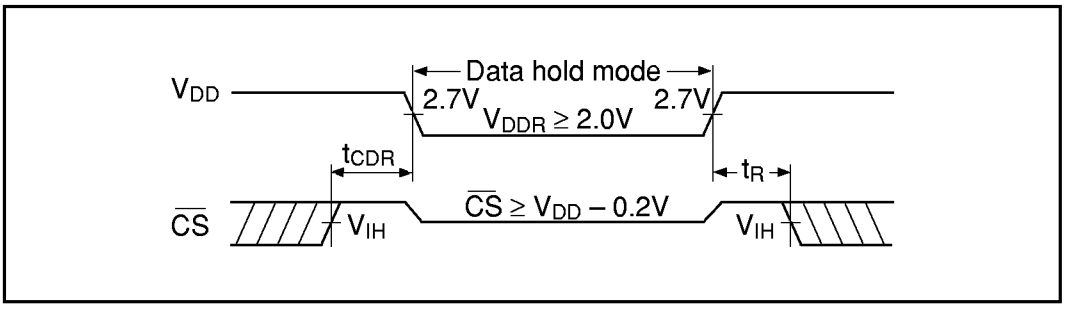
(V_{SS} = 0V, T_a = –25 to 85°C)

Parameter	Symbol	Conditions	Min	Typ*	Max	Unit
Data retention supply voltage	V_{DDR}		2.0	—	5.5	V
Data retention current	I_{DDR}	V_{DD} = 3V $\overline{CS} \geq V_{DD} - 0.2V$	—	0.25	20 (2**)	µA
Chip select data hold time	t_{CDR}		0	—	—	ns
Operation recovery time	t_R		5	—	—	ns

* Typical values are measured at 25°C

** Typical values are measured at 40°C

● Data Retention Timing



*Note: During standby mode in which the data is retentive, the supply voltage (V_{DD}) can be in low voltage until V_{DD} = V_{DDR}. At this mode, data reading and writing are impossible.

■ FUNCTIONS

● Truth Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	A0 to A14	Data I/O	Mode	IDD
H	X	X	—	Hi-Z	Standby	IDDS, IDDS1
L	X	L	Stable	DIN	Write	IDDA, IDDA1
L	L	H	Stable	DOUT	Read	IDDA, IDDA1
L	H	H	Stable	Hi-Z	Output disable	IDDA, IDDA1

X: "H" or "L"
—: "H", "L", or "Hi-Z"

● Read Mode

The data appear when the address is set while holding $\overline{CS}$ = "L", $\overline{OE}$ = "L" and $\overline{WE}$ = "H". When $\overline{OE}$ = "H", DATA I/O terminals are in high impedance state, that makes circuit design and bus control easy.

● Write Mode

There are the following 3 ways of writing data into memory:

(1) Hold $\overline{CS}$ = "L" and $\overline{WE}$ = "L", set address

(2) Hold $\overline{CS}$ = "L" then set address and give "L" pulse to $\overline{WE}$.

(3) After setting addresses, give "L" pulse to both $\overline{CS}$ and $\overline{WE}$.

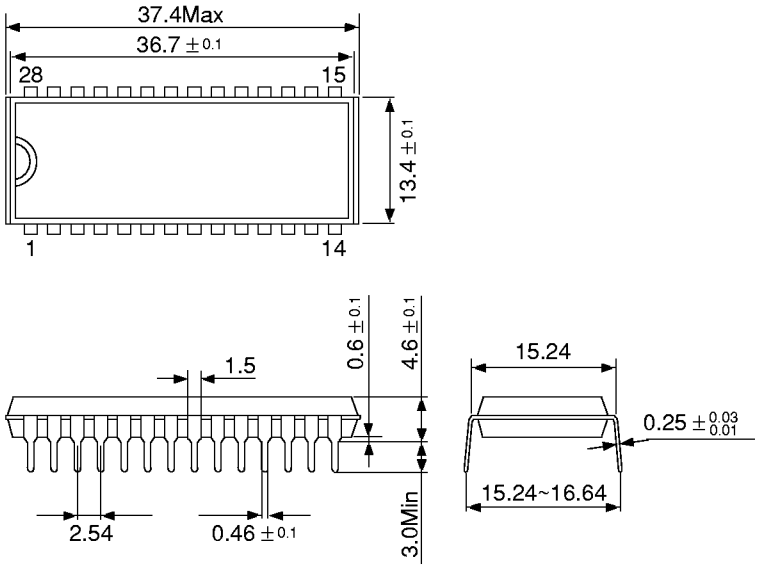
In case the above data on the DATA I/O terminals is latched up into the chip when $\overline{CS}$ or $\overline{WE}$ is in positive-going. Since DATA I/O terminals are high impedance when $\overline{CS}$ or $\overline{OE}$ = "H", bus contention between data driver and memory outputs can be avoided.

● Standby Mode

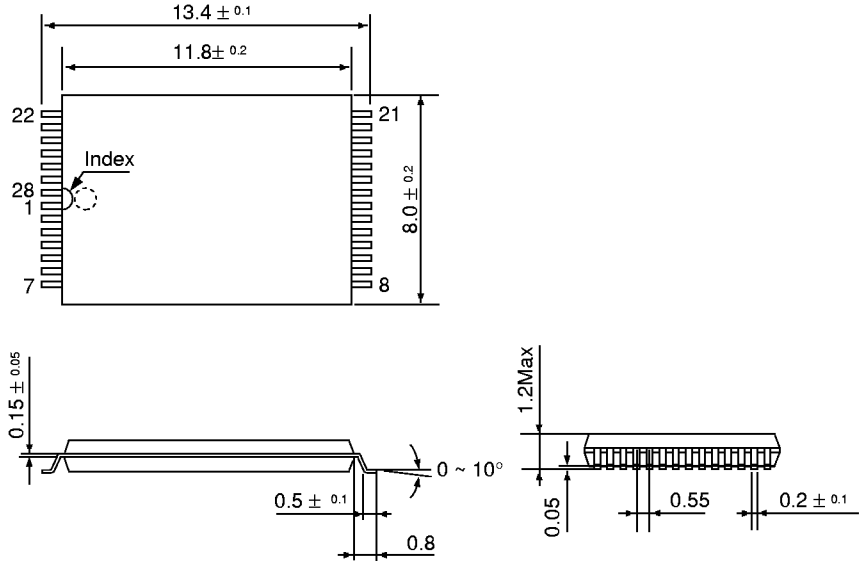
When $\overline{CS}$ is "H", the chip is in the standby mode. In this mode, DATA I/O terminals are high impedance and all inputs of addresses, $\overline{WE}$ and data can be any "H" or "L". When $\overline{CS}$ is over V_{DD}–0.2V, the chip is in the data retention battery backup mode. In this case, there is a small current in the chip which flows through the high resistances of the memory cells.

■ PACKAGE DIMENSIONS

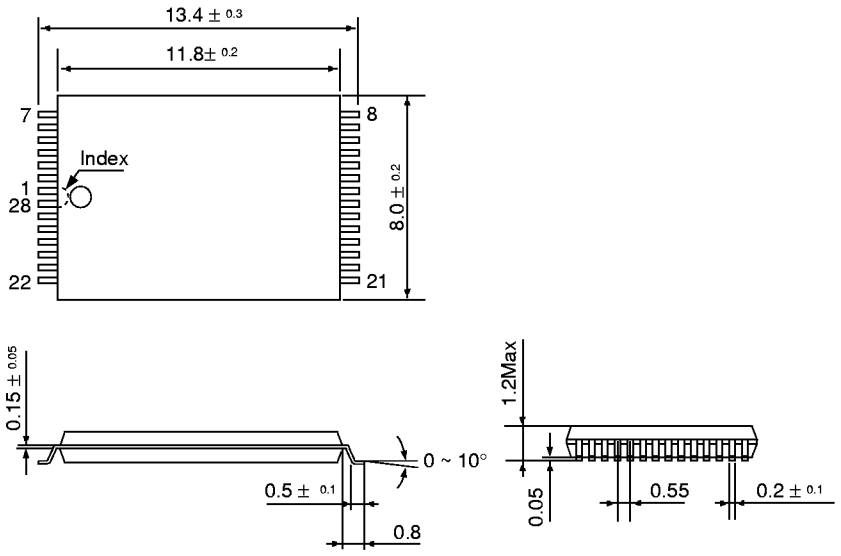
Plastic DIP-28 pin **Unit: mm (inch)**



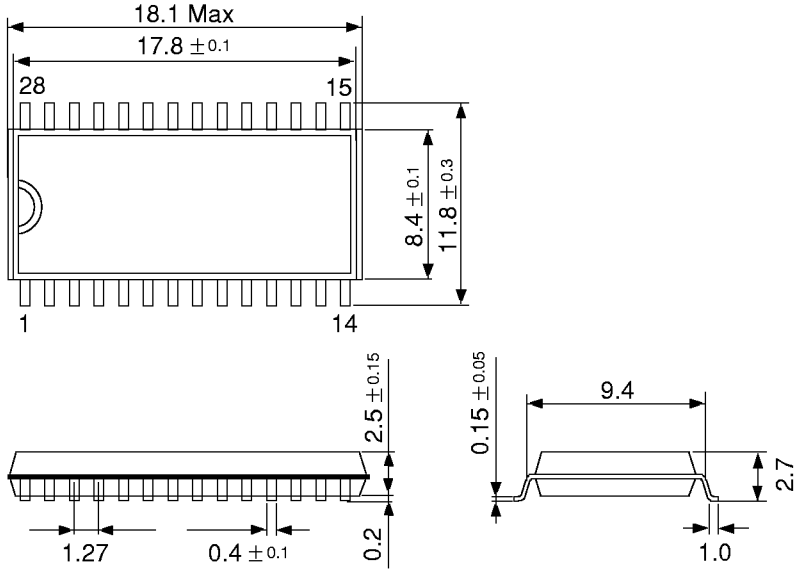
Plastic TSOP (I)-28 pin **Unit: mm (inch)**



Plastic TSOP (I)-28 pin-R1 **Unit: mm (inch)**



Plastic SOP2-28 pin **Unit: mm (inch)**



■ CHARACTERISTIC CURVES